

Date: - 8 Jan, 2007

Data Sheet Issue:- 1

#### **Provisional Data**

## **Rectifier Diode**

# Types W3842MC200 to W3842MC280

Development Type No.: WX199MC280

### **Absolute Maximum Ratings**

	VOLTAGE RATINGS	) [	MAXIMUM LIMITS	UNITS
$V_{RRM}$	Repetitive peak reverse voltage, (note 1)		2000-2800	V
$V_{RSM}$	Non-repetitive peak reverse voltage, (note 1)	1	2100-2900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)M}$	Maximum average forward current, T <sub>sink</sub> =55°C, (note 2)	3842	Α
$I_{F(AV)M}$	Maximum average forward current. T <sub>sink</sub> =100°C, (note 2)	2664	Α
$I_{F(AV)M}$	Maximum average forward current. T <sub>sink</sub> =100°C, (note 3)	1567	Α
I <sub>F(RMS)M</sub>	Nominal RMS forward current, T <sub>sink</sub> =25°C (note 2)	7067	Α
I <sub>F(d.c.)</sub>	D.C. forward current, T <sub>sink</sub> =25°C, (note 4)	6180	Α
I <sub>FSM</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>m</sub> =60%V <sub>RRM</sub> , (note 5)	35.1	kA
I <sub>FSM2</sub>	Peak non-repetitive surge t <sub>p</sub> ≠10ms, V <sub>rm</sub> ≤10V, (note 5)	38.6	kA
I <sup>2</sup> t	$l^2$ t capacity for fusing $t_p$ =10ms, $V_{rm}$ =60% $V_{RRM}$ , (note 5)	6.16×10 <sup>6</sup>	A <sup>2</sup> s
I <sup>2</sup> t	I <sup>2</sup> t capacity for fusing t <sub>p</sub> =10ms, V <sub>m</sub> ≤10V, (note 5)	7.45×10 <sup>6</sup>	A <sup>2</sup> s
T <sub>j op</sub>	Operating temperature range	-40 to +160	°C
$T_{stg}$	Storage temperature range	-55 to +160	°C

#### Notes:-

- 1) De-rating factor of 0.13% per °C is applicable for T<sub>j</sub> below 25°C.
- 2) Double side cooled, single phase, 50Hz, 180° half-sinewave.
- 3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled
- 5) Half-sinewave, 160°C J<sub>i</sub> initial.

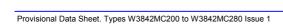


### **Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
$V_{FM}$	Maximum peak forward voltage	-	-	1.20	I <sub>FM</sub> =3000A	V
$V_{FM}$	Maximum peak forward voltage	-	-	1.75	I <sub>FM</sub> =8000A	V
$V_{T0}$	Threshold voltage	-	-	0.831	Valid from 2000A to 6000A	V
$r_{T}$	Slope resistance	-	-	0.118	Valid HOTT 2000A to 6000A	mΩ
I <sub>RRM</sub>	Peak reverse current	-	-	50	Rated V <sub>RRM</sub>	mA
$Q_{rr}$	Recovered charge	-	4200	-		μC
Q <sub>ra</sub>	Recovered charge, 50% Chord	-	3200	3600	I <sub>τM</sub> =1000A, t <sub>p</sub> =1000μs, di/dt=10A/μs,	μC
I <sub>rm</sub>	Reverse recovery current	-	190	- /	V <sub>r</sub> =106V	Α
t <sub>rr</sub>	Reverse recovery time, 50% chord	-	34	< - <		μs
		-	-	0.0140	Double side cooled	K/W
$R_{thJK}$	Thermal resistance, junction to heatsink	-	-	0.0265	Anode side cooled	K/W
			ı	0.0297	Cathode side cooled	K/W
F	Mounting force	25	- /	-31	Note 2	kN
$W_t$	Weight		530			g

#### Notes:-

- 1) Unless otherwise indicated  $T_j=160$  °C.
- 2) For other clamp forces, please consult factory.





#### **Notes on Ratings and Characteristics**

#### 1.0 Voltage Grade Table

Voltage Grade	V <sub>RRM</sub> V	V <sub>RSM</sub> V	V <sub>R</sub> DC V
20	2000	2100	1250
22	2200	2300	1350
24	2400	2500	1450
26	2600	2700	1550
28	2800	2900	1650

#### 2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales Production.

#### 3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T<sub>i</sub> below 25°C.

#### 4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

#### 5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{{V_{T0}}^2 + 4 \cdot ff^2} r_T \cdot W_{AV}}{2 \cdot ff^2 \cdot r_T}$$
 and:

$$W_{AV} = \frac{\Delta T}{R_{th}}$$
$$\Delta T = T_{t \max} - T_{K}$$

Where  $V_{T0}$ =0.831V,  $r_T$ =0.118m $\Omega$ ,

 $R_{\it th}$  = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

\ \ \ Supplementary Thermal Impedance					
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.	
Square wave Double Side Cooled	0.01665	0.01581	0.01516	0.0140	
Square wave Cathode Side Cooled	0.03217	0.03147	0.03090	0.0297	
Sine wave Double Side Cooled	0.01612	0.01531	0.01436		
Sine wave Cathode Side Cooled	0.03174	0.03105	0.03022		

Form Factors				
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.
Square wave	2.449	1.732	1.414	1
Sine wave	2.778	1.879	1.57	

#### 5.2 Calculating V<sub>F</sub> using ABCD Coefficients

The on-state characteristic I<sub>F</sub> vs. V<sub>F</sub>, on page 6 is represented in two ways;

- (i) the well established  $V_{T0}$  and  $r_T$  tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V<sub>F</sub>/ii terms of I<sub>F</sub> given below:

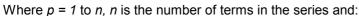
$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for  $V_F$  agree with the true device characteristic over a current range, which is limited to that plotted.

	25°C Coefficients	160°C Coefficients		
Α	0.7570696	Α	0.4876014	
В	0.01538751	В	0.02543331	
С	4.90758×10 <sup>-5</sup>	/ C_	6.37556×10 <sup>-5</sup>	
D	4.231663×10 <sup>-3</sup>	DQ /	5.796792×10 <sup>-3</sup>	

#### 5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$



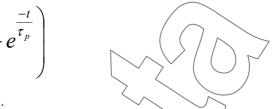
t = Duration of heating pulse in seconds.

r<sub>+</sub> = Thermal resistance at time t.

 $r_p$  = Amplitude of  $p_{th}$  term.

 $\tau_p$  = Time Constant of  $r_{th}$  term.

The coefficients for this device are shown in the tables below:



	D.C. Double Side Cooled							
Term	1	2	3	4				
$r_p$	8.594785×10 <sup>-3</sup>	3.308247×10 <sup>-3</sup>	1.039072×10 <sup>-3</sup>	7.916582×10 <sup>-4</sup>				
$ au_{\!p}$	0.7185764	0.09970181	0.02165834	5.266433×10 <sup>-3</sup>				

Term	1	2//	3
$r_p$	0.02196926	5.845724×10 <sup>3</sup>	1.904897×10 <sup>-3</sup>
$ au_{p}$	4.127141	0.1629998	8.832583×10 <sup>-3</sup>

#### 6.0 Reverse recovery ratings

(i) Q<sub>ra</sub> is based on 50% I<sub>m</sub> chord as shown in Fig. 1

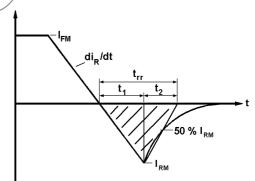
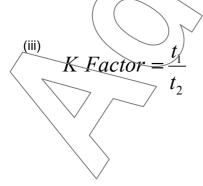


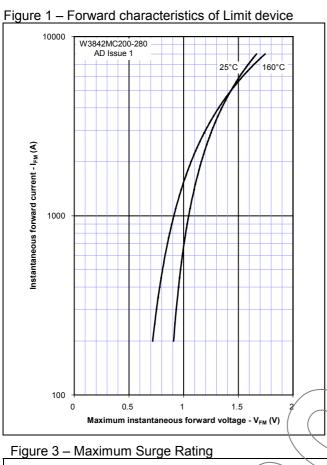
Fig. 1

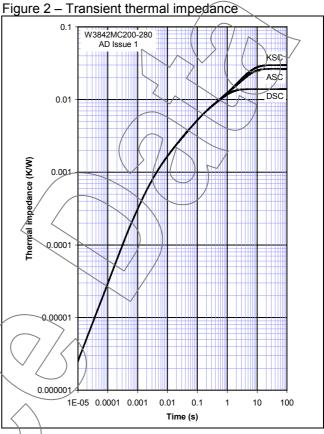
(ii) 
$$Q_{rr}$$
 is based on a 150 $\mu$ s integration time i.e.



$$Q_{rr} = \int_{0}^{150 \,\mu s} i_{rr}.dt$$

#### **Curves**





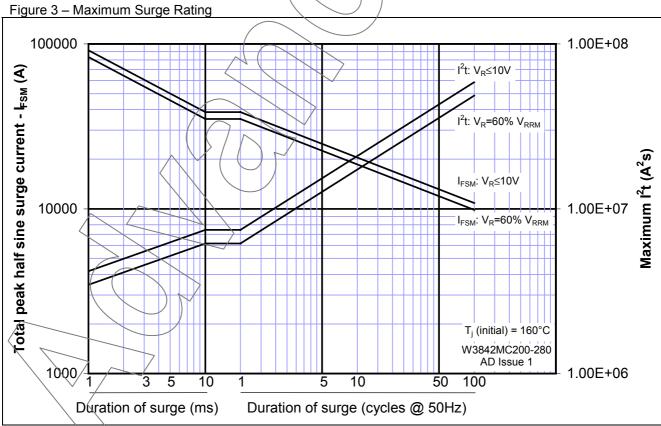


Figure 4 – Total recovered charge, Q<sub>rr</sub>

100000

W3842MC200-280
AD Issue 1
T<sub>j</sub> = 160°C

10000

10000

10000

10000

Commutation rate - di/dt (A/µs)

Figure 5 – Recovered charge, Q<sub>ra</sub> (50% chord)

10000

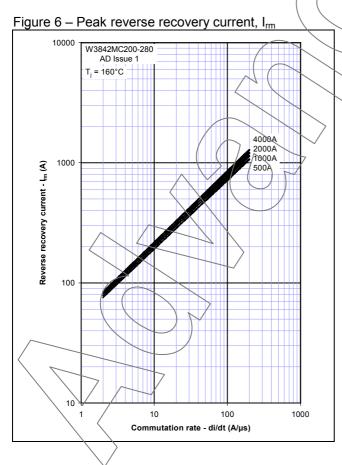
W3842MC200-280
AD Issue 1
T<sub>j</sub> = 160°C

1000A

500A

1000A

Commutation rate - di/dt (A/µs)



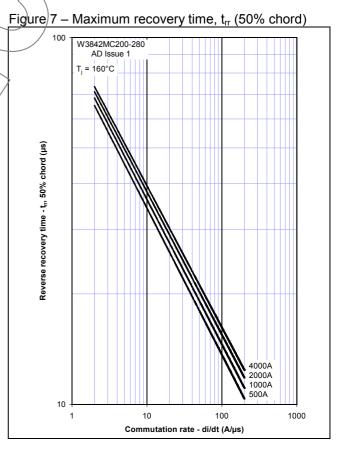


Figure 8 – Forward current vs. Power dissipation – Double Side Cooled

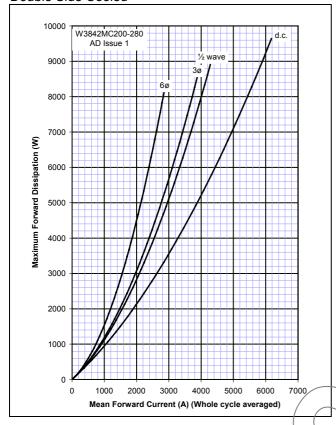


Figure 10 – Forward current vs. Power dissipation – Cathode Side Cooled

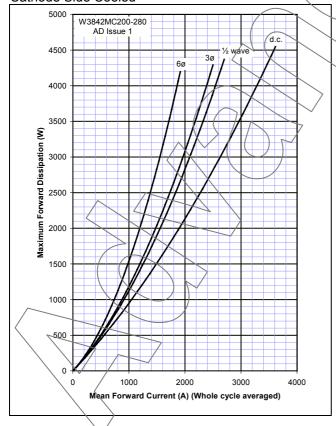


Figure 9 – Forward current vs. Heatsink temperature – Double Side Cooled

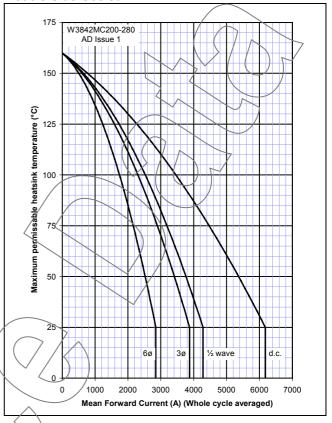
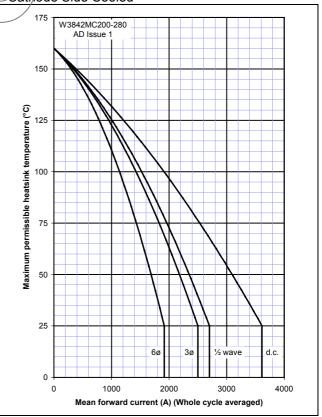
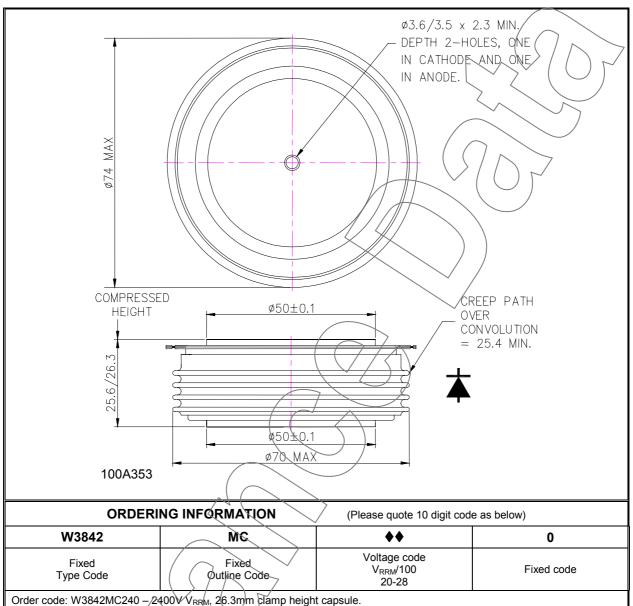


Figure 11 – Forward current vs. Heatsink temperature — Cathode Side Cooled



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